

READOUT AND REWRITE-IN METHOD FOR DYNAMIC MOS SEMICONDUCTOR MEMORY

Veröffentlichungsnummer JP57018080

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Anmelder: MITSUBISHI ELECTRIC CORP

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- Internationale: G11C11/407; G11C11/408; G11C11/407;
G11C11/408; (IPC1-7): G11C11/34

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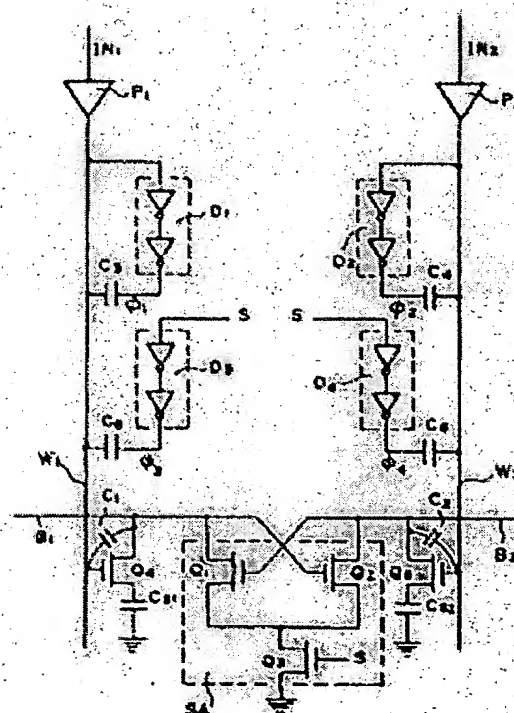
Prioritätsnummer(n): JP19800093451 19800707

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Zusammenfassung von JP57018080

PURPOSE: To assure the readout and rewrite-in voltage to a memory cell, by boosting the word line drive pulse more than the power supply voltage before the operation of sense amplifier circuit and boosting it once more after the operation of the sense amplifier circuit.

CONSTITUTION: First, boosting capacitors C3, C4 are charged with boosting pulses ϕ_1 , ϕ_2 outputted from delay circuits D1, D2 after a given time through the input of word line drive pulse WP, to boost the word lines W1, W2. Further, a sense amplifier, drive signal S is inputted to delay circuits D3, D4 and word line boosting pulses ϕ_3 , ϕ_4 is outputted after a given time. The boosting capacitors C3, C6 are charged with the word line boosting pulses ϕ_3 , ϕ_4 and the word lines W1, W2 are boosted again. Thus, the potential of the word lines W1, W2 can be assured sufficiently highly.



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